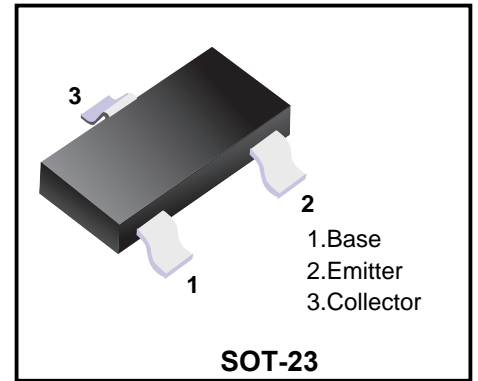


**PNP Transistors**

**Features**

- ◆ Low equivalent on-resistance

Marking Code	
FMMT591	591



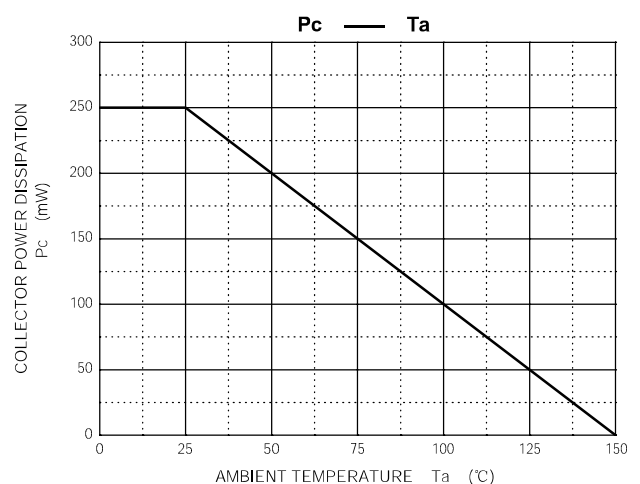
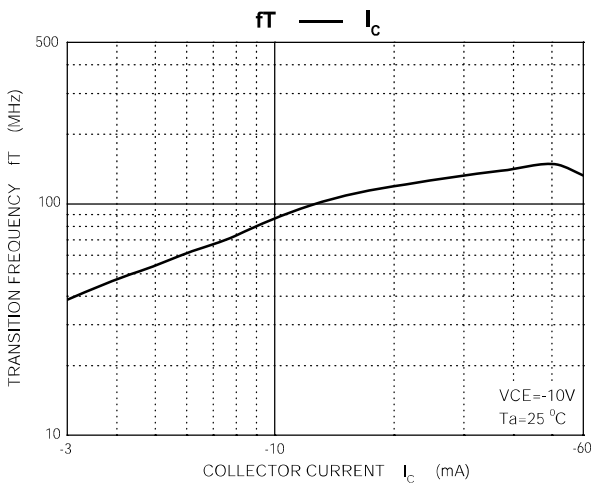
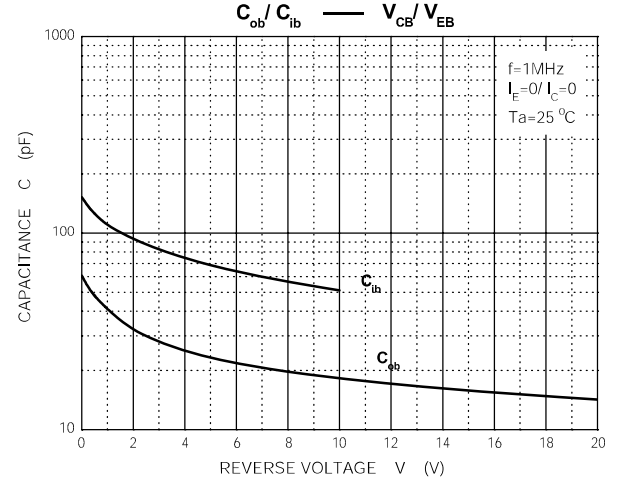
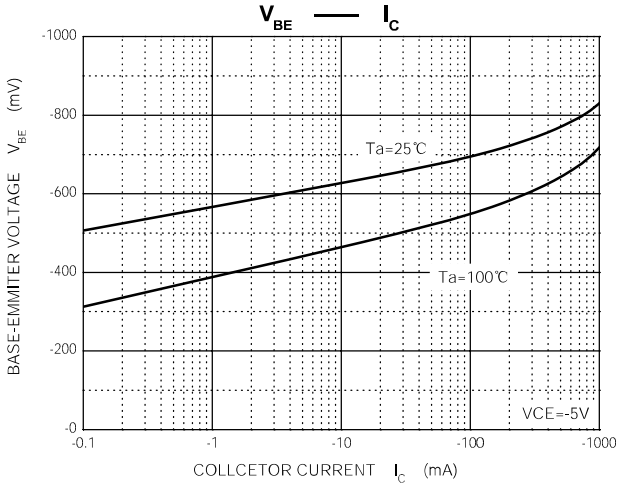
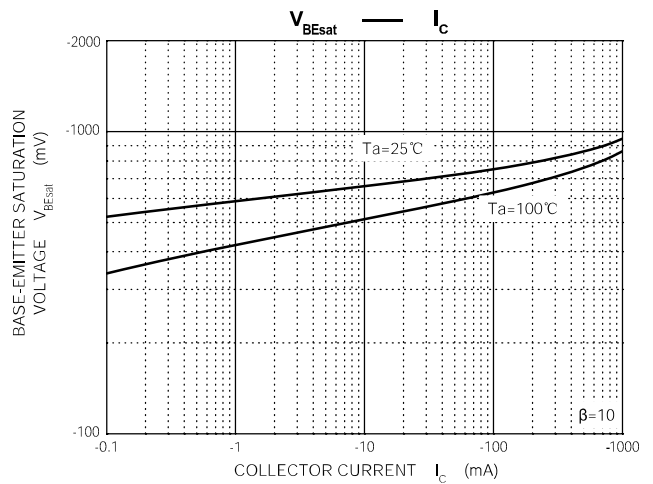
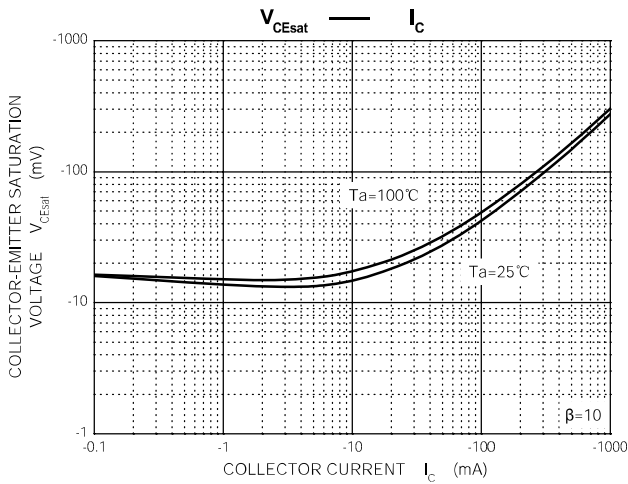
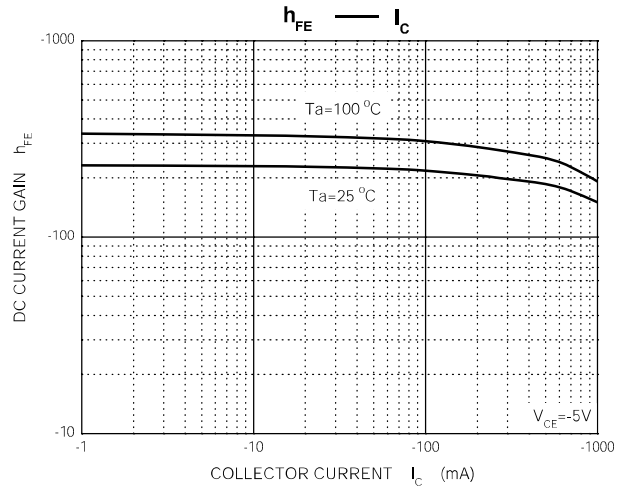
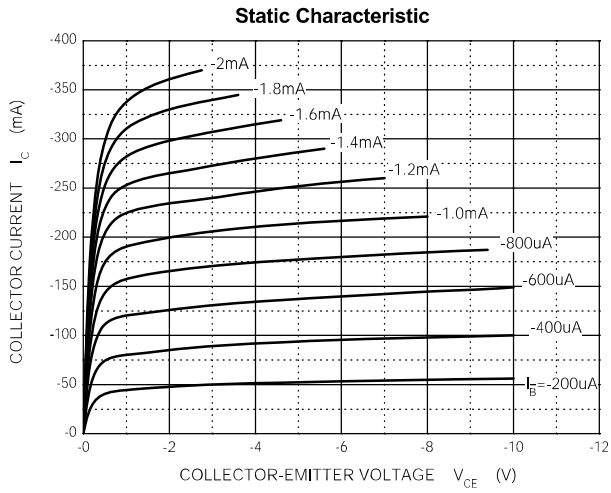
**Maximum Ratings (Ta=25°C unless otherwise specified.)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-1	A
I <sub>CM</sub>	Peak Pulse Current	-2	A
P <sub>C</sub>	Collector Power Dissipation	250	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	500	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

**Electrical Characteristics (Ta=25°C unless otherwise specified.)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-80			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> <sup>1</sup>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	100			
	h <sub>FE(2)</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-500mA	100		300	
	h <sub>FE(3)</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A	80			
	h <sub>FE(4)</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-2A	15			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub> <sup>1</sup>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-0.3	V
	V <sub>CE(sat)2</sub> <sup>1</sup>	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> <sup>1</sup>	I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA			-1.2	V
Base-emitter voltage	V <sub>BE</sub> <sup>1</sup>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA, f=100MHz	150			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz			10	pF

<sup>1</sup>Measured under pulsed conditions, Pulse width=300μs, Duty cycle≤2%.



**Ordering information**

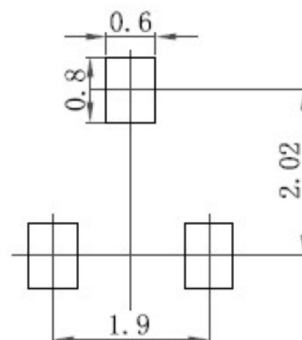
Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

**Package Dimensions**

**SOT-23**

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118
E	1.2	1.4	47	55
E	1.9		75	
E1	0.95		37	
HE	2.1	2.55	83	100
Lp	0.15	0.45	5.9	18
Q	0.45	0.55	18	22
v	0.2		7.9	
W	0.1		4	

**The recommended mounting pad size**



## Disclaimer

The information presented in this document is for reference only. Guangdong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.